

Silicon NPN Power Transistors

BU2525A

DESCRIPTION

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- With TO-3PN package
- High voltage
- High speed switching

APPLICATIONS

- For use in horizontal deflection circuits of large screen colour TV receivers.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

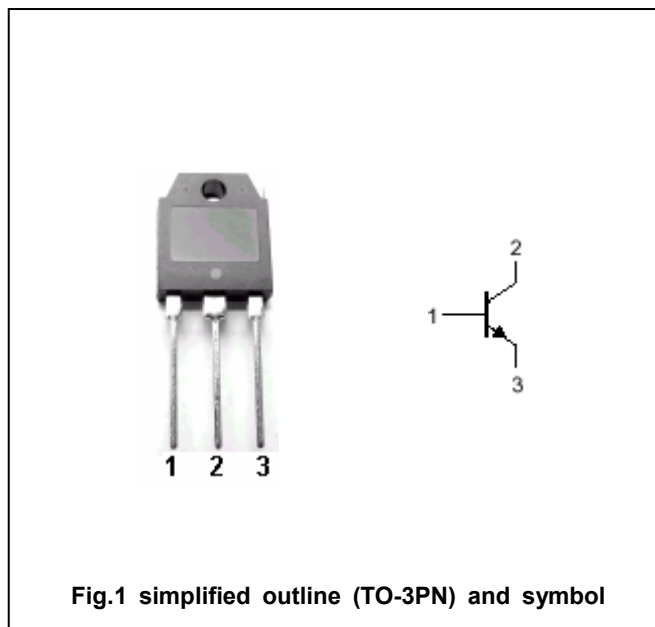


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	7.5	V
I _C	Collector current (DC)		12	A
I _{CM}	Collector current -peak		30	A
I _B	Base current(DC)		8	A
I _{BM}	Base current -peak		12	A
P _C	Collector power dissipation	T _C =25°C	125	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

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CHARACTERISTICS

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 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=100\text{mA}; I_B=0, L=25\text{mH}$	800			
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1\text{mA}; I_C=0$	7.5	13.5		V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=8\text{A}; I_B=1.6\text{A}$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=8\text{A}; I_B=1.6\text{A}$			1.3	V
I_{CES}	Collector cut-off current	$V_{CE}=\text{rated}; V_{BE}=0$ $T_j=125^\circ\text{C}$			1.0 2.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=7.5\text{V}; I_C=0$			1.0	mA
h_{FE-1}	DC current gain	$I_C=0.1\text{A}; V_{CE}=5\text{V}$	6	13	26	
h_{FE-2}	DC current gain	$I_C=8\text{A}; V_{CE}=5\text{V}$	5	7	10	
C_C	Collector capacitance	$I_E=0, V_{CB}=10\text{V}; f=1\text{MHz}$		145		pF

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PACKAGE OUTLINE

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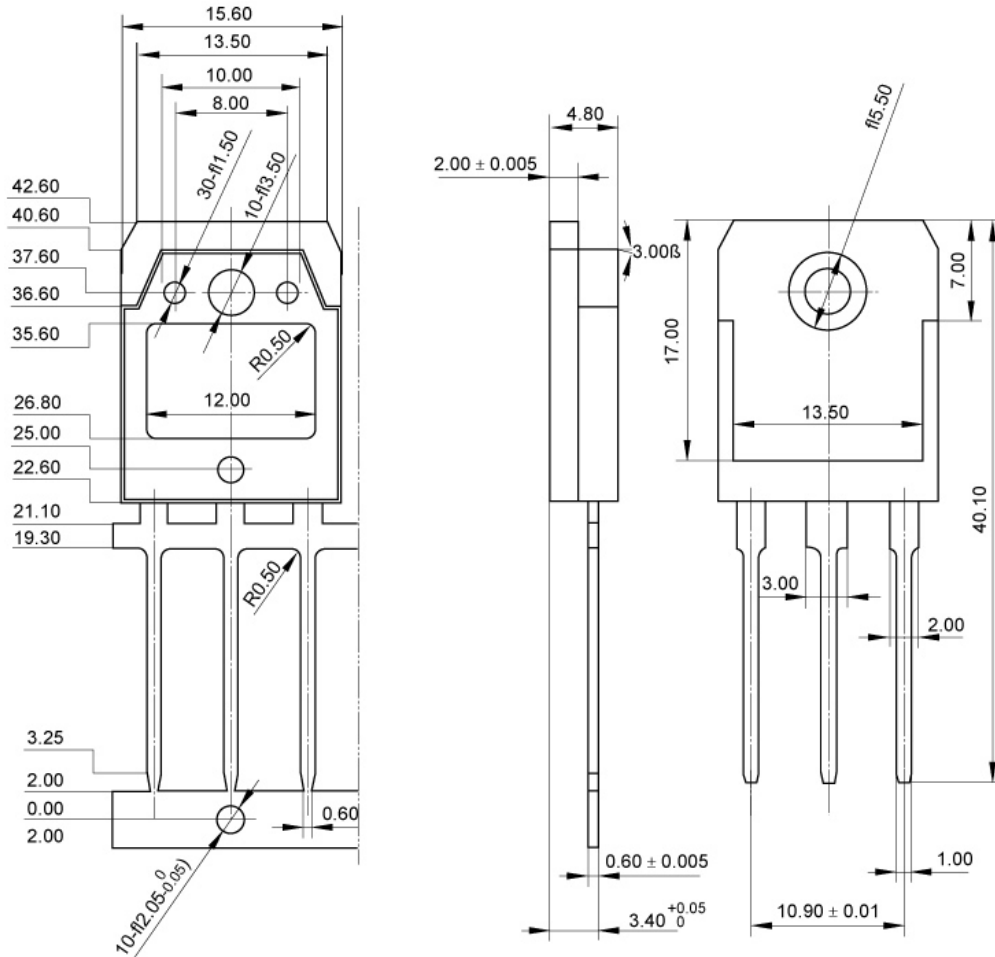


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)